



Micro Commercial Components
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BUP22C

Features

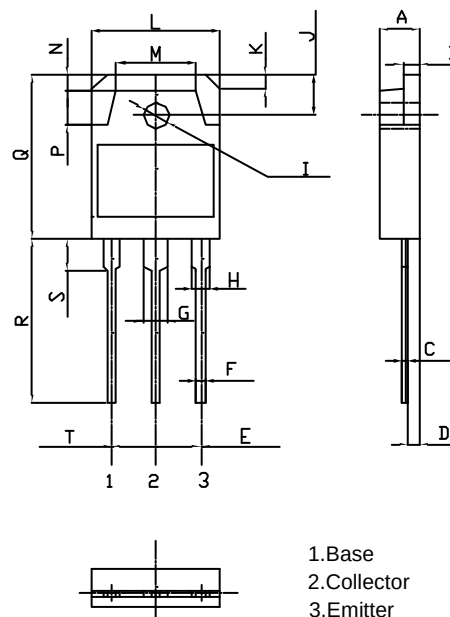
- High voltage
- With TO-3PN package
- NPN Silicon power transistor intended for high voltage, high speed switching industrial applications.

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	450	V
V_{CBO}	Collector-Base Voltage	850	V
I_{CP}	Peak Collector Current	20	A
I_C	Collector Current	8.0	A
P_C	Collector power dissipation	125	W
T_J	Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

NPN Silicon Power Transistors

TO-3PN



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=100\text{mA}$, $I_B=0$)	450	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=850\text{Vdc}$, $I_E=0$)	---	1.0	mA
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=9.0\text{Vdc}$, $I_C=0$)	---	10	mA

ON CHARACTERISTICS

h_{FE}	Forward Current Transfer ratio ($I_C=1.0\text{A}$, $V_{CE}=5.0\text{Vdc}$)	10	50	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=6.0\text{A}$, $I_B=1.2\text{A}$)	---	1.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=6.0\text{A}$, $I_B=1.2\text{A}$)	---	1.5	Vdc
t_F	Fall Time ($I_C=6.0\text{A}$, $I_{B1}=I_{B2}=1.2\text{A}$)	---	0.8	us
t_S	Turn-Off Storage Time ($I_C=6.0\text{A}$, $I_{B1}=I_{B2}=1.2\text{A}$)	---	4.0	us

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.161	.197	4.80	5.00	
B	.074	.083	1.90	2.10	
C	.022	.033	0.55	0.85	
D	.211	.219	5.35	5.55	
E	.037	.049	0.95	1.25	
F	.118	.125	3.00	3.18	
G	.079	.083	2.00	2.11	
H	.122	.130	3.10	3.30	
I	.189	.205	4.80	5.20	
J	.071	.075	1.80	1.91	
K	.598	.630	15.20	16.00	
L	.378	.396	9.6	10.05	
M	.079	.083	2.0	2.11	
N	.157	.161	4.0	4.1	
O	.772	.795	19.6	20.2	
P	.787	.800	20.0	20.3	
Q	.157	.161	4.0	4.1	
R	.211	.219	5.35	5.55	
S	.037	.049	0.95	1.25	
T	.037	.049	0.95	1.25	